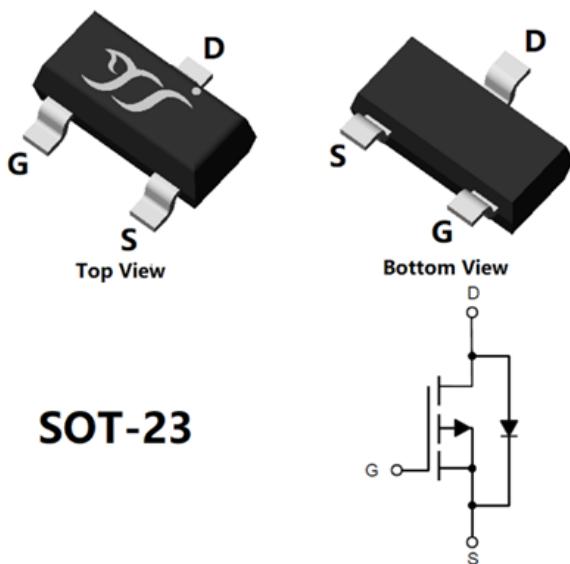




P-Channel Enhancement Mode Field Effect Transistor



Product Summary

• V_{DS}	-40V
• I_D	-3A
• $R_{DS(ON)}$ (at $V_{GS}=-10V$)	<80mΩ
• $R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	<110mΩ

General Description

- Trench Power LV MOSFET technology
- High Speed switching
- Halogen Free
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Power switching application
- Uninterruptible power supply
- PWM application

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	-40	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_A=25^\circ C$	I_D	-3	A
	$T_A=100^\circ C$		-1.9	
Pulsed Drain Current ^A		I_{DM}	-20	A
Total Power Dissipation ^B	$T_A=25^\circ C$	P_D	1	W
	$T_A=100^\circ C$		0.4	
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	°C

Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^C	Steady-State	$R_{\theta JA}$	100	120	°C/W

Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJL03P04A	F2	03P04.	3000	30000	120000	7 " reel



YJL03P04A

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =-250µA	-40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-40V, V _{GS} =0V	-	-	-1	µA
		V _{DS} =-40V, V _{GS} =0V, T _J =150°C	-	-	-100	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =-250µA	-1	-1.5	-2.5	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-3A	-	61	80	mΩ
		V _{GS} =-4.5V, I _D =-2A	-	81	110	
Diode Forward Voltage	V _{SD}	I _S =-3A, V _{GS} =0V	-	-0.85	-1.2	V
Gate resistance	R _G	f=1MHz	-	20	-	Ω
Maximum Body-Diode Continuous Current	I _S		-	-	-3	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =-20V, V _{GS} =0V, f=1MHz	-	400	-	pF
Output Capacitance	C _{oss}		-	50	-	
Reverse Transfer Capacitance	C _{rss}		-	40	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =-10V, V _{DS} =-20V, I _D =-3A	-	8.5	-	nC
Gate-Source Charge	Q _{gs}		-	1	-	
Gate-Drain Charge	Q _{gd}		-	2	-	
Reverse Recovery Charge	Q _{rr}	I _F =-3A, di/dt=100A/us	-	31	-	nC
Reverse Recovery Time	t _{rr}		-	34	-	ns
Turn-on Delay Time	t _{D(on)}	V _{GS} =-10V, V _{DD} =-20V, I _D =-3A R _{GEN} =3Ω	-	6	-	ns
Turn-on Rise Time	t _r		-	6	-	
Turn-off Delay Time	t _{D(off)}		-	31	-	
Turn-off fall Time	t _f		-	19	-	

- A. Repetitive rating; pulse width limited by max. junction temperature.
- B. P_d is based on max. junction temperature, using junction-case thermal resistance.
- C. The value of R_{θJA} is measured with the device mounted on the minimum recommend pad size, in the still air environment with T_A=25°C. The maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.

■Typical Electrical and Thermal Characteristics Diagrams

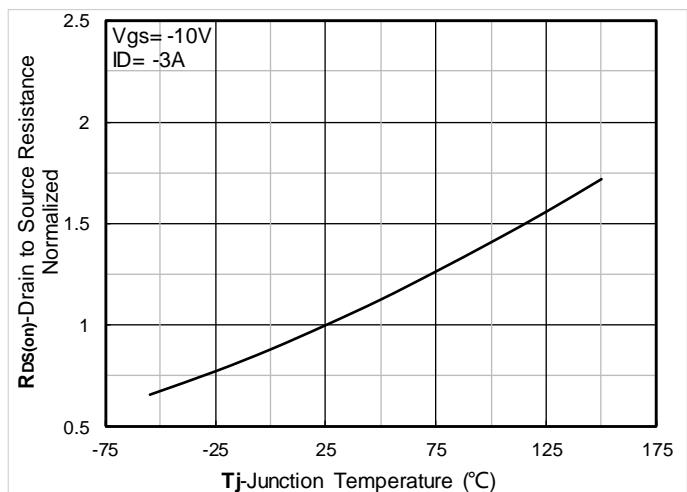
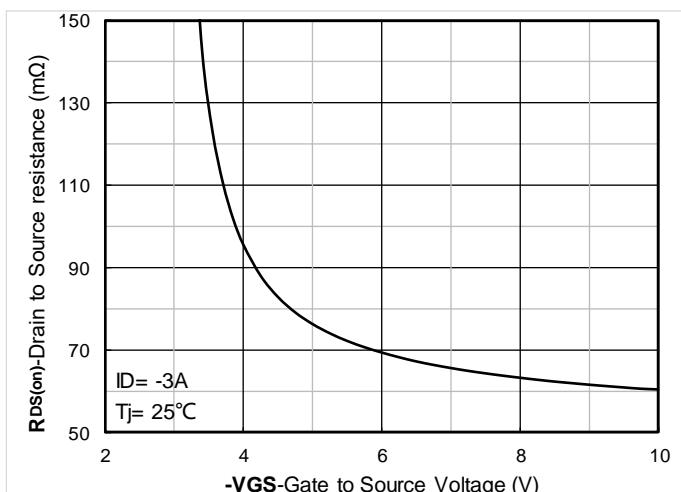
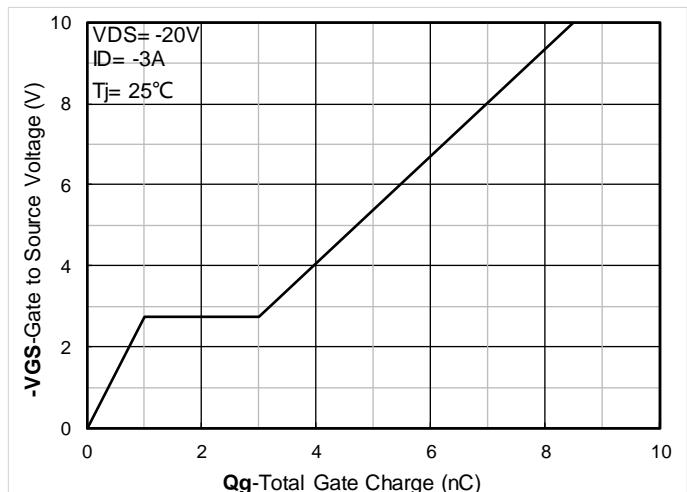
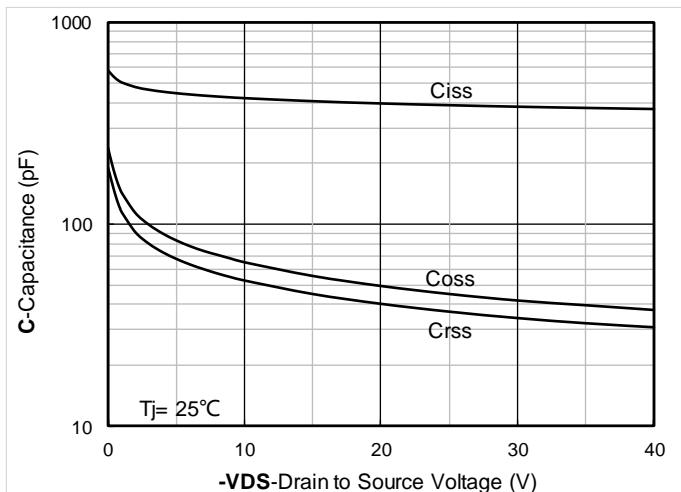
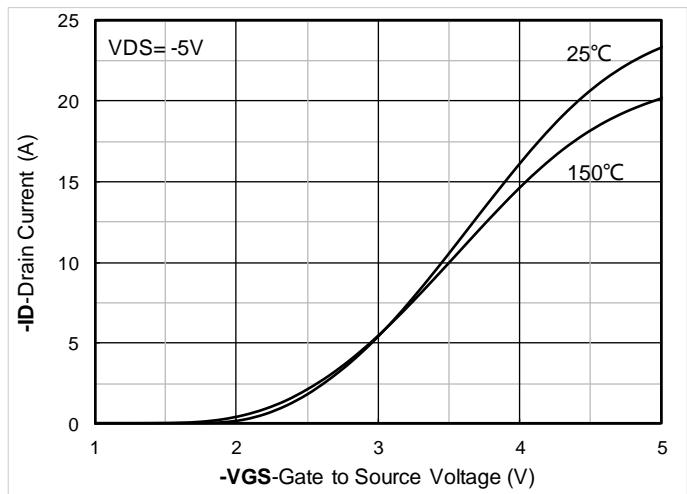
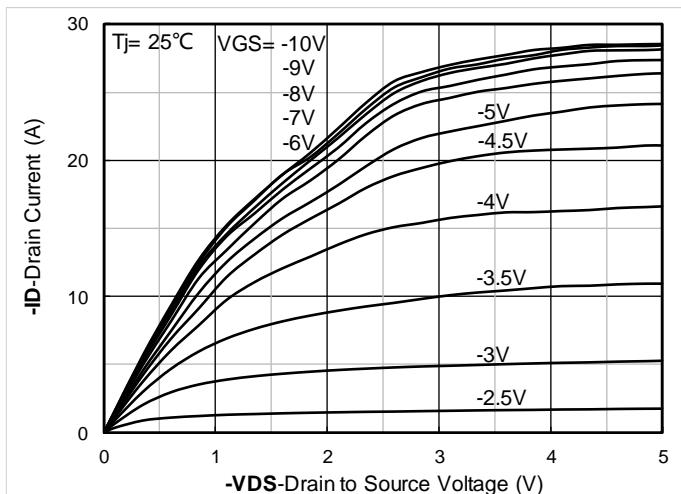


Figure 5. On-Resistance vs Gate to Source Voltage

Figure 6. Normalized On-Resistance



YJL03P04A

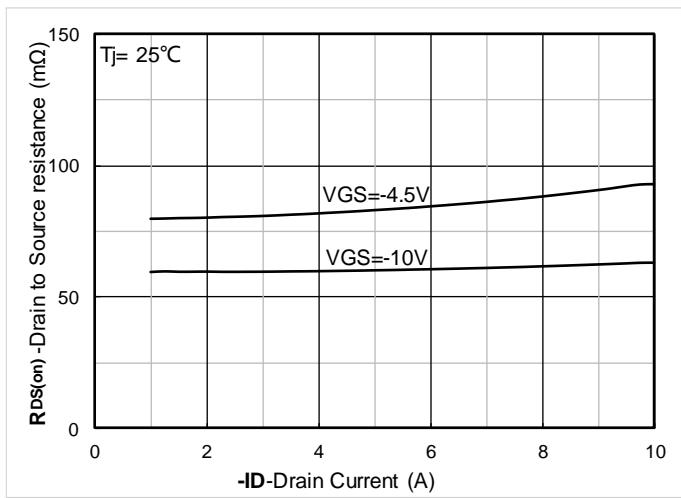


Figure 7. $R_{DS(on)}$ VS Drain Current

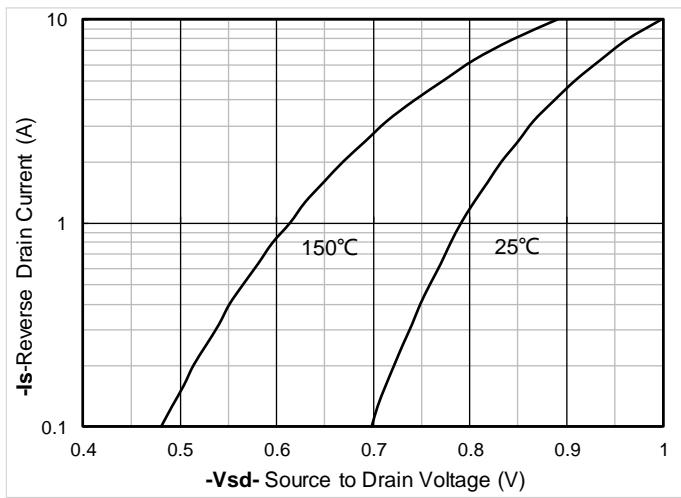


Figure 8. Forward characteristics of reverse diode

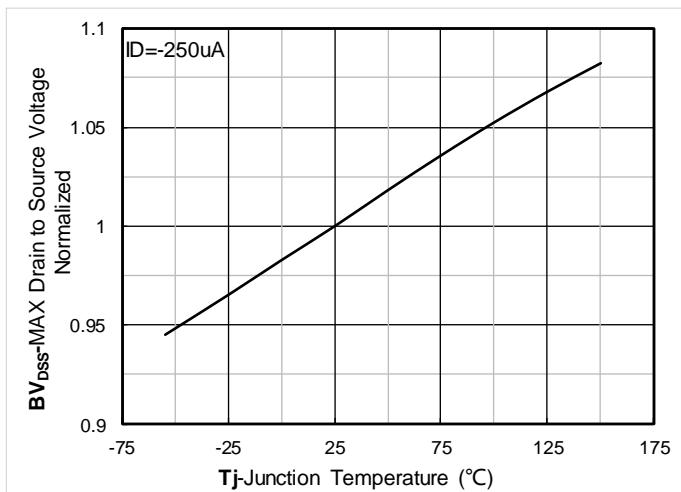


Figure 9. Normalized breakdown voltage

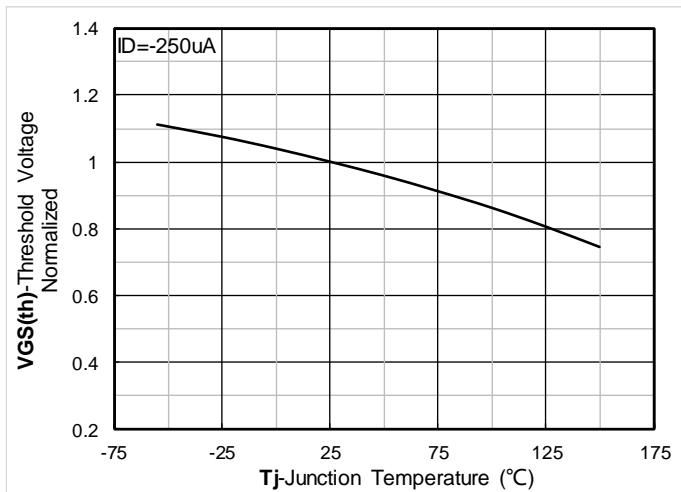


Figure 10. Normalized Threshold voltage

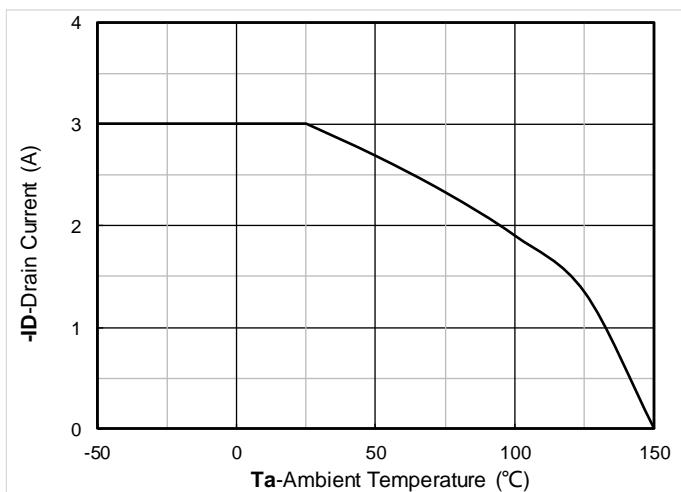


Figure 11. Current dissipation

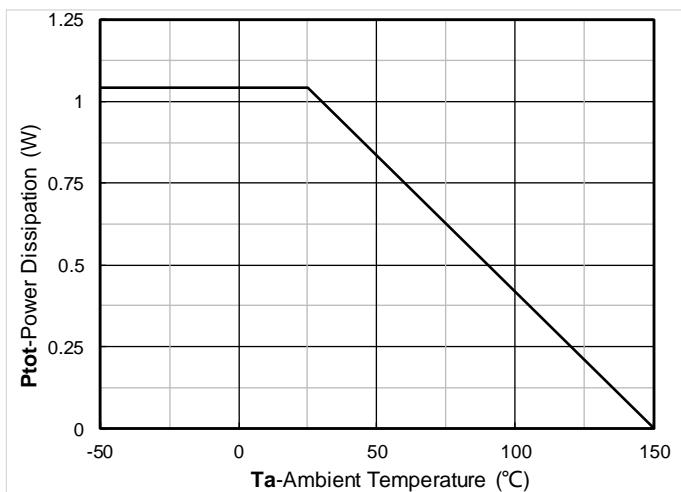
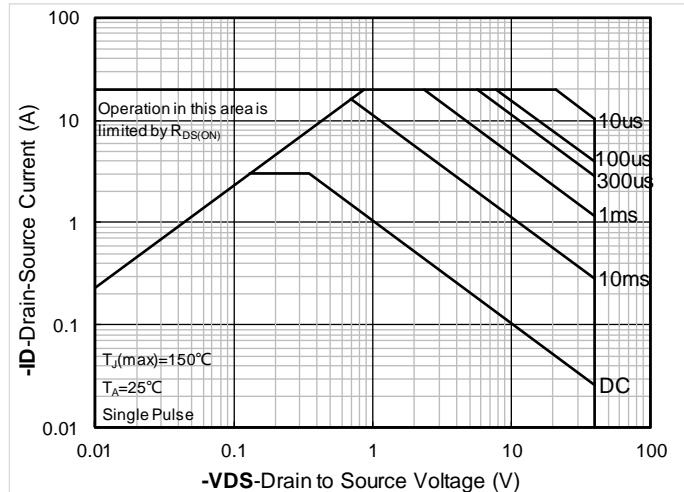
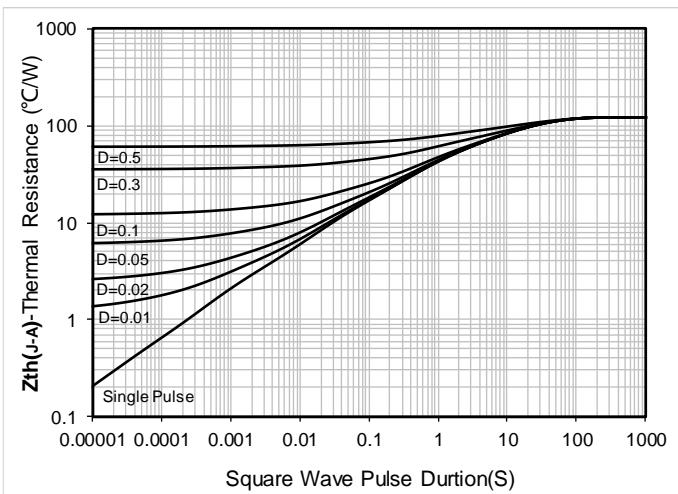
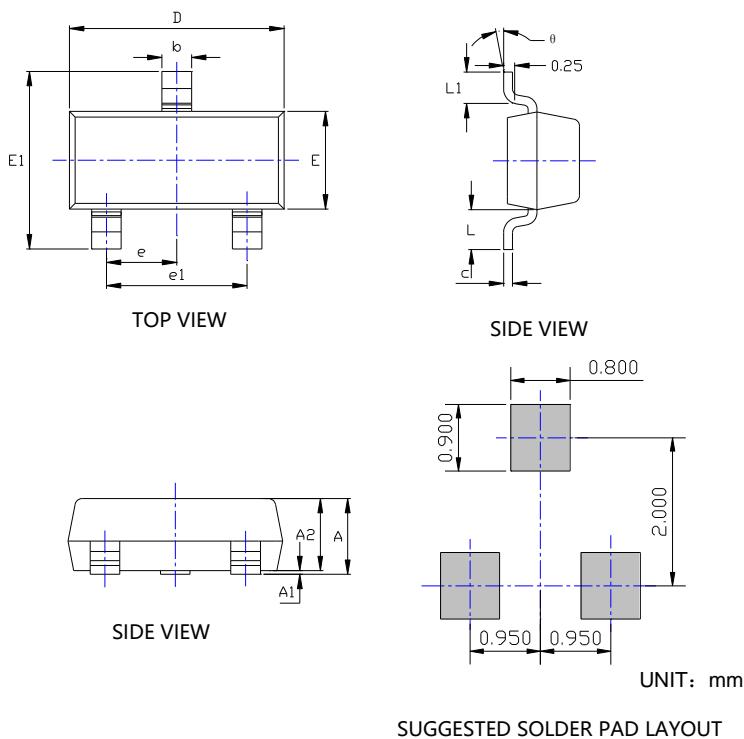


Figure 12. Power dissipation



**■ SOT-23 Package information**

SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.035	0.045	0.900	1.150
A1	0.000	0.004	0.000	0.100
A2	0.035	0.041	0.900	1.050
b	0.012	0.020	0.300	0.500
c	0.004	0.008	0.100	0.200
D	0.110	0.118	2.800	3.000
E	0.047	0.055	1.200	1.400
E1	0.089	0.100	2.250	2.550
e	0.037TYP		0.950TYP	
e1	0.071	0.079	1.800	2.000
L	0.022REF		0.550REF	
L1	0.012	0.020	0.300	0.500
θ	0°	8°	0°	8°

NOTE:

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



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